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Memorandum

PARAMAX
A Unisys Company

DATE: October 20, 1992

PPM-92-251

TO: D. Kapoor/311.1

FROM: K. Sahu/7809 ks

SUBJECT: Radiation Report on TOMS/C4 Project.
Part No. MD82C59AB7011 (control no.5822)

cc: R. Shelley/303
A. Sharma/311
A. Casasnovas
✓ Library/300.1

A radiation evaluation was performed on the MD82C59AB7011 (82C59) Programmable Priority Interrupt Controller to determine the total dose tolerance of these parts. A brief summary of the test results is provided below. For detailed information, refer to Tables I through IV and Figure 1.

The total dose testing was performed on four samples, using a cobalt-60 gamma-ray source. One part was used as a control sample. The total dose radiation steps were 2.5, 5, 10, 15, 20 and 30 krads (the term rad as used here means rad(Si)). The dose rate was between 0.07 and 0.5 krads/hour, depending on the total dose level (see Table II for radiation schedule). The parts were kept under bias during irradiation and annealing treatments (see Figure 1 for bias configuration). After the 20-krad exposure, the parts were annealed at +25°C for 168 hours and 288 hours (cumulative). After these annealing steps, the parts were irradiated to a total accumulated dose of 30 krads. Finally, the parts were annealed for 168 hours at +100°C. After each radiation exposure and annealing treatment, the parts were electrically tested at +25°C according to the test conditions and the specification limits listed in Table III. These tests included two functional tests at 1.36 MHz and three functional tests at 1 MHz.

All five parts passed the initial electrical tests. All four irradiated parts passed all electrical tests up to the 10 krad exposure. After the 10-krad irradiation, all parts exceeded the maximum specification limit of 10uA for ICCSBH and ICCSBL, with readings between 46uA and 72uA. These values decreased after the 15 krad exposure to between 31uA and 39uA. After the 20-krad irradiation, the values for ICCSBH and ICCSBL ranged between 37uA and 46uA.

After 168 hours of annealing at 25°C, one part recovered to within the maximum specification limits for ICCSBH and ICCSBL and the other two parts had readings of 20uA. On continued annealing to 288 hours (cumulative), two parts recovered to within the maximum specification limits for ICCSBH and ICCSBL and the other parts had readings of 19uA. On further irradiation to 30 krads, all four parts exceeded the maximum specification limits, with readings of 45uA. After annealing for 168 hours at +100°C, all parts passed all electrical tests. No rebound effects were observed after annealing at 100°C.

All parts passed all functional tests throughout all irradiation and annealing steps.

Table IV gives the mean and standard deviation values for each parameter after different irradiation exposures and annealing steps.

Any further details about this evaluation can be obtained upon request. If you have any questions, please call me at (301) 731-8954.

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TABLE I. Part Information

Generic Part Number:	82C59
TOMS/C4 Part Number:	MD82C59AB7011
Control Number:	5822
Charge Number:	C24005
Manufacturer:	Harris Corporation
Lot Date Code:	8902
Quantity Tested:	5
Serial Number of Radiation Samples:	223, 224, 225, 227
Serial Number of Control Sample:	222
Part Function:	Programmable Priority Interrupt Controller
Part Technology:	CMOS
Package Style:	28-pin DIP
Test Engineer:	A. Karygiannis

TABLE II. Radiation Schedule for 82C59

EVENTS	DATE
1) INITIAL (PRE-IRRADIATION) ELECTRICAL MEASUREMENT	09/04/92
2) 2.5- KRAD IRRADIATION (0.11 krads/hour) POST-2.5-KRAD ELECTRICAL MEASUREMENT	09/15/92 09/16/92
3) 5-KRAD IRRADIATION (0.13 krads/hour) POST-5-KRAD ELECTRICAL MEASUREMENT	09/16/92 09/17/92
4) 10-KRAD IRRADIATION (0.25 krads/hour) POST-10-KRAD ELECTRICAL MEASUREMENT	09/17/92 09/18/92
5) 15-KRAD IRRADIATION (0.07 krads/hour) POST-15-KRAD ELECTRICAL MEASUREMENT	09/18, 92 09/21/92
6) 20-KRAD IRRADIATION (0.26 krads/hour) POST-20-KRAD ELECTRICAL MEASUREMENT	09/21/92 09/22/92
7) 168 HOURS ANNEALING AT +25°C POST-168-HOUR ELECTRICAL MEASUREMENTS	09/22/92 10/01/92
8) 288 HOURS (CUMULATIVE) ANNEALING AT +25°C POST-120-HOUR ELECTRICAL MEASUREMENTS	10/02/92 10/06/92
8) 30-KRAD IRRADIATION (0.5 krads/hour) POST-30-KRAD ELECTRICAL MEASUREMENT	10/06/92 10/07/92
9) 168 HOURS ANNEALING AT +100°C POST-168-HOUR ELECTRICAL MEASUREMENT	10/07/92 10/15/92
ALL ELECTRICAL MEASUREMENTS WERE PERFORMED AT +25°C.	
PARTS WERE IRRADIATED AND ANNEALED UNDER BIAS; SEE FIGURE 1.	

Table III. Electrical Characteristics of 82C59

TESTS PERFORMED								
PARAMETER	VCC	VIL	VIH	CONDITIONS	PINS	LIMITS AT +25C, -55C, +125C		
FUNC1	4.5V	0.4V	2.6V	FREQ = 1.36MHz	ALL I/O	VOL<1.5V / VDH>1.5V		
FUNC2	4.5V	0.4V	2.6V	FREQ = 1.00MHz	ALL I/O	VOL<1.5V / VDH>1.5V		
FUNC3	5.5V	0.4V	2.6V	FREQ = 1.36MHz	ALL I/O	VOL<1.5V / VDH>1.5V		
FUNC4	5.5V	0.4V	2.6V	FREQ = 1.00MHz	ALL I/O	VOL<1.5V / VDH>1.5V		
FUNC5	5.5V	0.0V	5.5V	FREQ = 1.00MHz	ALL I/O	VOL<0.4V / VDH>3.0V		

PARAMETER	VCC	VIL	VIH	CONDITIONS	PINS	LIMITS AT +25C, -55C, +125C		
VDH1	4.5V	0.6V	2.2V	LOAD=-2.5mA	DUTS	>+3.0V / <+5.5V		
VDH2	4.5V	0.6V	2.2V	LOAD=-100uA	DUTS	>+4.1V / <+5.5V		
VOL	4.5V	0.6V	2.2V	LOAD=+2.5mA	DUTS	>+0.0V / <+0.4V		
IIH	5.5V	0.0V	5.5V	VTST= 5.5V	INS	>+0.0A / <+1.0UA		
IIH_IR	5.5V	0.0V	5.5V	VTST= 5.5V	IR INS	>+0.0A / <+100A		
IIL	5.5V	0.0V	5.5V	VTST= 0.0V	INS	>-1.0UA / <+0.0A		
IIL_IR	5.5V	0.0V	5.5V	VTST= 0.0V	IR INS	>-500uA / <+0.0A		
IOZH	5.5V	0.0V	5.5V	VOUT= 5.5V	DUTS	>-100A / <+100A		
IOZL	5.5V	0.0V	5.5V	VOUT= 0.	DUTS	>-100A / <+100A		
ICCSBH	5.5V	0.0V	5.5V	VIN = 5.5V	VCC	>+0.0A / <+100A		
ICCSBL	5.5V	0.0V	5.5V	VIN = 0.0V	VCC	>+0.0A / <+100A		

PARAMETER	ABSOLUTE DELTA LIMITS AT +25C				PERCENTAGE DELTA LIMITS @ +25C			
VDH1	>-100mV	/	<+100mV		>-20%	/	<+20%	
VDH2	>-100mV	/	<+100mV		>-20%	/	<+20%	
VOL	>-40mV	/	<+40mV		>-20%	/	<+20%	
IIH	>-100nA	/	<+100nA		>-20%	/	<+20%	
IIH_IR	>-1uA	/	<+1uA		>-20%	/	<+20%	
IIL	>-100nA	/	<+100nA		>-20%	/	<+20%	
IIL_IR	>-500uA	/	<+500uA		>-20%	/	<+20%	
IOZH	>-1uA	/	<+1uA		>-20%	/	<+20%	
IOZL	>-1uA	/	<+1uA		>-20%	/	<+20%	
ICCSBH	>-1uA	/	<+1uA		>-20%	/	<+20%	
ICCSBL	>-1uA	/	<+1uA		>-20%	/	<+20%	

PARAMETER	VCC	VIL	VIH	CONDITIONS	PINS	LIMITS AT +25C, -55C, +125C		
TRLDVH_1	4.5V	0.4V	2.6V	C=1 / VCMP=1.5V	RD/INTA->D	>0.0NS / <160.0NS		
TRLDVL_1	4.5V	0.4V	2.6V	C=1 / VCMP=1.5V	RD/INTA->D	>0.0NS / <160.0NS		
TRHDLZ_1	4.5V	0.4V	2.6V	C=2 / VCMP=VOL+.5V	RD/INTA->D	>10.0NS / <100.0NS		
TRHDHZ_1	4.5V	0.4V	2.6V	C=2 / VCMP=VDH-.5V	RD/INTA->D	>10.0NS / <100.0NS		
TJH1H_1	4.5V	0.4V	2.6V	C=1 / VCMP=1.5V	IR->INT	>0.0NS / <350.0NS		
TIALCV_1	4.5V	0.4V	2.6V	C=1 / VCMP=1.5V	INTA->CAS	>0.0NS / <565.0NS		
TRLELI_1	4.5V	0.4V	2.6V	C=1 / VCMP=1.5V	INTA->EN	>0.0NS / <125.0NS		
TRHEHI_1	4.5V	0.4V	2.6V	C=1 / VCMP=1.5V	INTA->EN	>0.0NS / <60.0NS		
TRLELK_1	4.5V	0.4V	2.6V	C=1 / VCMP=1.5V	RD->EN	>0.0NS / <125.0NS		
TRHEHR_1	4.5V	0.4V	2.6V	C=1 / VCMP=1.5V	RD->EN	>0.0NS / <60.0NS		
TAHDVH_1	4.5V	0.4V	2.6V	C=1 / VCMP=1.5V	CS->D	>0.0NS / <210.0NS		
TAHDVL_1	4.5V	0.4V	2.6V	C=1 / VCMP=1.5V	CS->D	>0.0NS / <210.0NS		
TCVDVH_1	4.5V	0.4V	2.6V	C=1 / VCMP=1.5V	CAS->D	>0.0NS / <300.0NS		
TCVDVL_1	4.5V	0.4V	2.6V	C=1 / VCMP=1.5V	CAS->D	>0.0NS / <300.0NS		

PARAMETER	VCC	VIL	VIH	CONDITIONS	PINS	LIMITS AT +25C, -55C, +125C		
TRLDVH_2	5.5V	0.4V	2.6V	C=1 / VCMP=1.5V	RD/INTA->D	>0.0NS / <160.0NS		
TRLDVL_2	5.5V	0.4V	2.6V	C=1 / VCMP=1.5V	RD/INTA->D	>0.0NS / <160.0NS		
TRHDLZ_2	5.5V	0.4V	2.6V	C=2 / VCMP=VOL+.5V	RD/INTA->D	>10.0NS / <100.0NS		
TRHDHZ_2	5.5V	0.4V	2.6V	C=2 / VCMP=VDH-.5V	RD/INTA->D	>10.0NS / <100.0NS		
TJH1H_2	5.5V	0.4V	2.6V	C=1 / VCMP=1.5V	IR->INT	>0.0NS / <350.0NS		
TIALCV_2	5.5V	0.4V	2.6V	C=1 / VCMP=1.5V	INTA->CAS	>0.0NS / <565.0NS		
TRLELI_2	5.5V	0.4V	2.6V	C=1 / VCMP=1.5V	INTA->EN	>0.0NS / <125.0NS		
TRHEHI_2	5.5V	0.4V	2.6V	C=1 / VCMP=1.5V	INTA->EN	>0.0NS / <60.0NS		
TRLELK_2	5.5V	0.4V	2.6V	C=1 / VCMP=1.5V	RD->EN	>0.0NS / <125.0NS		
TRHEHK_2	5.5V	0.4V	2.6V	C=1 / VCMP=1.5V	RD->EN	>0.0NS / <60.0NS		
TAHDVH_2	5.5V	0.4V	2.6V	C=1 / VCMP=1.5V	CS->D	>0.0NS / <210.0NS		
TAHDVL_2	5.5V	0.4V	2.6V	C=1 / VCMP=1.5V	CS->D	>0.0NS / <210.0NS		
TCVDVH_2	5.5V	0.4V	2.6V	C=1 / VCMP=1.5V	CAS->D	>0.0NS / <300.0NS		
TCVDVL_2	5.5V	0.4V	2.6V	C=1 / VCMP=1.5V	CAS->D	>0.0NS / <300.0NS		

Table III. Electrical Characteristics of 82C59 - cont.

LOAD USED	V1	AC PARAMETRIC TEST LOAD CONDITIONS									
OUT-----	K1	TEST CONDITION	V1	R1	R2	SWT1					
/ SWT1		C=1	1.7V	523	--	OPEN					
K2		C=2	VCC	1.8K	1.8K	CLOSED					
GND		COMMENTS/EXCEPTIONS									
(1) THESE PARAMETERS WERE TESTED DURING FUNCTIONAL # 1 AND #3 AS GO/NOGO : - tAHRL, tRHAX, tRLRH, tAHWL, tWHAX, tWLWH, - tDVWH, tWHDX, tJLJH, tCVIAL, tRHRL, tWHWL & tCHCL											
(2) VIL & VIH WERE TESTED DURING VOL & VOH TESTS AS GO/NOGO.											
(3) DUE TO S-50 (ATE) LIMITATIONS, ALL PROPAGATION DELAYS AND TRI-STATE MEASUREMENTS WERE MADE WITH A CAPACITIVE LOAD (CL) OF APPROXIMATELY 5UpF to 60pF (STRAY CAPACITANCE OF THE TABLE).											
(4) {JL} ADDED PERCENTAGE DELTA LIMITS ON 10-07-91.											
HARDWARE REQUIREMENTS			TEST TEMPERATURES								
DEVICE CONFIGURATION : 28-PIN DIP	S-50 LOAD BOARD # 12 : CLOSE DIP SWITCH FOR DUT	PIN 14 (GND).	25 DEG. C.	X	-55 DEG. C.	X					
			125 DEG. C.	X							
PROGRAMMER : JUAN RAFAEL LANDER			DATE : 05-15-89		UPDATE : 10-07-91	{JL}					

TABLE IV: Summary of Electrical Measurements After
Total Dose Exposures and Annealing for MD82C59AB7011 1/

Parameters	Spec Limit	Total Dose Exposure (TDE) (krads)*						Anneal			TDE			Anneal		
		0 (Pre-Rad) mean min max	5 mean sd	10 mean sd	15 mean sd	20 mean sd	168 hrs @25°C mean sd	288 hrs @25°C mean sd	30 krad mean sd	168 hrs @100°C mean sd						
FUNC1	4.5V, 1.36MHz	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass		
FUNC2	4.5V, 1.00MHz	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass		
FUNC3	5.5V, 1.36MHz	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass		
FUNC4	5.5V, 1.00MHz	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass		
FUNC4	5.5V, 1.00MHz	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass		
VOH1	V	3	5.5	4.38	.01	4.38	.02	4.38	.02	4.37	.01	4.38	.01	4.38	.01	
VOH2	V	4.1	5.5	4.49	0	4.49	.01	4.49	.02	4.48	0	4.49	0	4.49	0	
VOL	mV	0	400	85.4	14	86.6	15	88.2	17	87.5	17	51.2	187	89.8	17	
IIH	uA	0	1	0	0	0	0	0	0	0	0	0	0	0	0	
IIH IR	uA	0	10	0.78	0.1	0.67	0.1	0.61	0.1	**	**	0.60	0.1	0.54	0.08	
III	uA	-1	0	0	0	0	0	0	0	0	0	0	0	0	0	
III IR	uA	-500	0	-140	3.7	-134	3.8	-128	4.1	-127	3.9	-125	3.8	-124	4.2	
IOZH	uA	-10	10	0	0	0	0.01	0.01	0.01	0.03	0.04	0.01	0.01	0.09	0.1	
IOZL	uA	-10	10	0	0	0	0	0	0	0	0	0	0	0	0	
ICCSBH	uA	0	10	0	0	0	57.0	9.4	37.0	3.5	46.0	0	10.0	9.50	45.0	
ICCSBL	uA	0	10	0	0	0	52.5	7.1	33.0	3.5	37.0	0	10.0	4.75	8.2	
TRLDVH 1 ns	0	160	41.9	3.8	41.6	3.8	42.0	3.9	42.6	4.0	43.1	4.0	43.4	4.1	43.9	
TRLDVL 1 ns	0	160	42.0	2.5	41.9	2.6	42.4	2.6	42.7	2.7	43.2	2.7	43.6	2.8	43.9	
TRHDLZ 1 ns	10	100	49.8	2.7	49.4	2.7	49.3	2.7	49.1	2.6	49.1	2.6	49.7	2.6	49.4	
TRHDHZ 1 ns	10	100	51.5	5.2	52.0	5.2	52.5	5.5	52.8	5.5	53.2	5.5	53.6	5.4	53.1	
TOIH	1 ns	0	350	58.7	2.4	58.5	2.4	58.5	2.3	59.4	2.5	59.9	2.5	60.9	2.5	60.8
TIALCV 1 ns	0	565	33.2	1.0	32.9	1.0	33.2	1.0	33.8	1.1	34.3	1.0	34.6	1.1	35.1	
TRLELI 1 ns	0	125	41.9	1.1	41.9	1.1	42.9	1.1	42.8	1.1	43.4	1.1	43.9	1.1	44.9	
TRHEHI 1 ns	0	50	27.9	0.8	27.7	0.8	27.6	0.9	27.6	0.8	27.7	0.8	28.2	0.8	27.8	
TRLELR 1 ns	0	125	33.5	0.8	33.2	0.8	33.6	0.7	33.5	0.7	33.8	0.7	34.3	0.8	34.7	
TRHEHR 1 ns	0	50	31.6	0.8	31.5	0.8	31.6	0.8	31.8	0.8	31.9	0.8	32.3	0.9	32.1	
TAHDVH 1 ns	0	210	48.7	2.3	48.1	2.4	48.2	2.5	48.6	2.6	48.9	2.7	49.2	2.7	49.9	
TAHDVL 1 ns	0	210	47.6	1.7	47.1	1.8	47.3	1.8	47.4	1.8	47.5	1.9	48.2	1.9	48.2	

TABLE IV (cont.): Summary of Electrical Measurements After Total Dose Exposures and Annealing for MD82C59AB7011 1/

Parameters	Total Dose Exposure (TDE) (krads)												Anneal 168 hrs @100°C	TDE 30 krads	Anneal 168 hrs @25°C			
	0		5		10		15		20		168 hrs @25°C							
	Spec Limit (Pre-Rad)	mean sd	mean sd															
TCVDVH_1 ns	0	300	66.3	10	65.9	10	66.3	10	67.1	10	67.7	10	68.4	10	68.9	10		
TCVDVL_1 ns	0	300	45.7	13	46.6	13	47.1	13	47.5	13	48.1	14	48.5	14	48.7	14		
TRLDVH_2 ns	0	160	35.9	3.1	35.5	3.2	35.9	3.2	36.3	3.3	36.7	3.3	36.9	3.4	37.4	3.4		
TRLDVL_2 ns	0	160	36.4	2.3	36.2	2.3	36.6	2.4	36.7	2.4	37.1	2.5	37.4	2.5	37.6	2.6		
TRHDLL_2 ns	10	100	45.6	2.8	45.2	2.8	45.0	2.8	44.9	2.7	44.9	2.7	45.3	2.7	45.0	2.6		
TRHDHZ_2 ns	10	100	48.3	5.4	49.0	5.4	49.3	5.5	49.4	5.7	49.8	5.7	50.1	5.6	49.7	5.6		
TOHIIH_2 ns	0	350	49.3	1.9	49.0	1.9	49.1	1.9	49.6	1.8	49.9	1.9	50.6	1.9	50.3	1.8		
TIALCV_2 ns	0	565	28.3	0.8	27.9	0.8	28.1	0.8	28.5	0.8	28.8	0.8	29.4	1.6	29.5	0.8		
TRLELI_2 ns	0	125	36.9	0.8	36.8	0.9	37.6	0.8	37.5	0.8	37.9	0.9	38.2	0.9	38.9	0.9		
TRHEHI_2 ns	0	50	24.9	0.6	24.6	0.6	24.5	0.6	24.5	0.6	24.9	0.6	24.5	0.6	24.3	0.6		
TRLELR_2 ns	0	125	29.9	0.6	29.5	0.6	29.9	0.7	29.7	0.6	29.8	0.6	30.3	0.6	30.2	0.6		
TRHEHR_2 ns	0	50	28.3	0.6	28.3	0.6	28.2	0.6	28.3	0.6	28.3	0.7	28.7	0.7	28.5	0.6		
TAHDVH_2 ns	0	210	44.3	2.0	43.7	2.1	44.0	2.2	44.1	2.2	44.3	2.3	44.6	2.3	45.1	2.3		
TAHDVL_2 ns	0	210	43.3	1.5	42.8	1.6	43.0	1.6	42.9	1.6	43.0	1.7	43.4	1.7	43.6	1.7		
TCVDVH_2 ns	0	300	57.5	8.8	57.0	8.8	57.3	8.7	57.6	8.7	58.1	8.7	58.5	8.8	59.0	8.7		
TCVDVL_2 ns	0	300	40.7	12	40.5	12	40.9	13	41.1	13	41.5	13	41.8	13	42.0	13		

Notes:

1/ The mean and standard deviation values were calculated over the four parts irradiated in this testing. The control samples remained constant throughout the testing and are not included in this table.

*The 2.5-krad exposure produced no significant change in parameters and is omitted for clarity.
**No reliable reading was obtainable at this point.

Figure 1. Radiation Bias Circuit for 82C59

